



Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	3.5	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V } R_L=33\Omega$	I - II - III	MAX.	25	mA
$V_{GT}$		I - II - III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II - III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III	MAX.	40	mA
		II		60	
$I_H$	$I_T=100\text{mA}$		MAX.	35	mA
dV/dt	$V_D=670\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	1500	V/ $\mu\text{s}$
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =20V/ $\mu\text{s}$ , $T_j=125^\circ\text{C}$		MIN.	8	A/ms
$t_{on}$	$I_G=40\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	5	$\mu\text{s}$
$t_{off}$				70	
$V_{CL}$	$I_{CL}=0.1\text{mA } t_p=1\text{ms}$		MIN.	1050	V

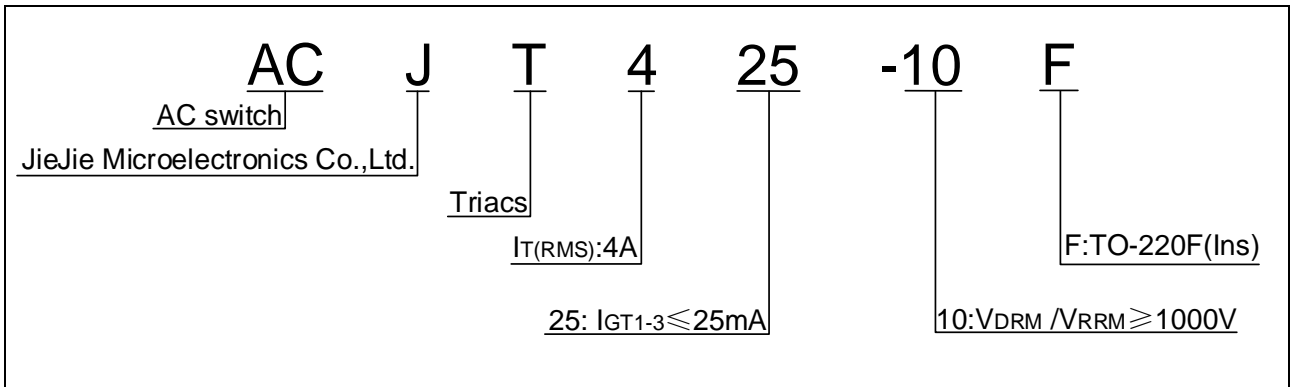
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=5.6\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.73	V
$R_D$	Dynamic resistance	$T_j=125^\circ\text{C}$	171	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	8	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	0.4	mA

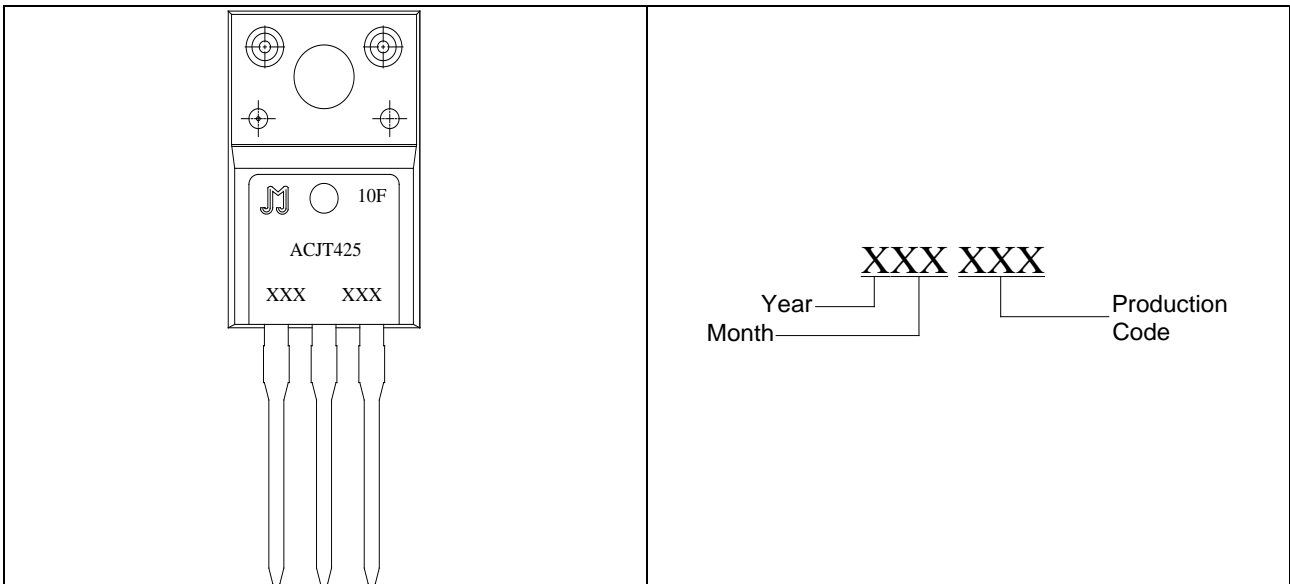
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3.5	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C/W}$

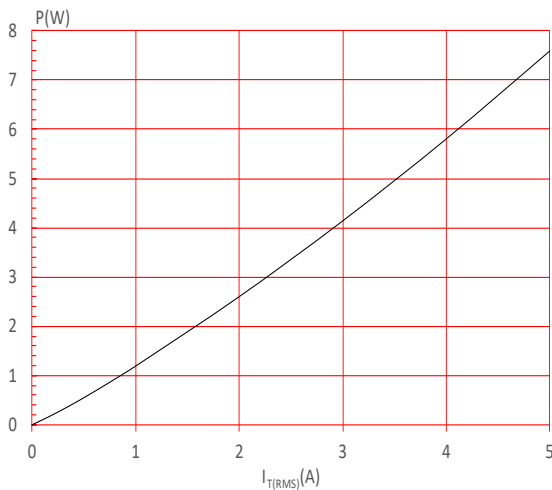
ORDERING INFORMATION



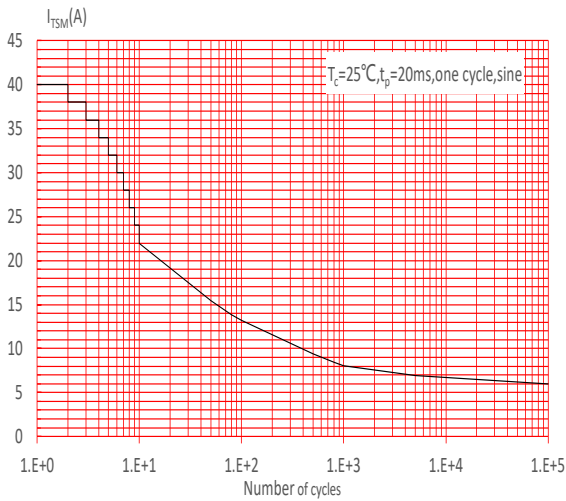
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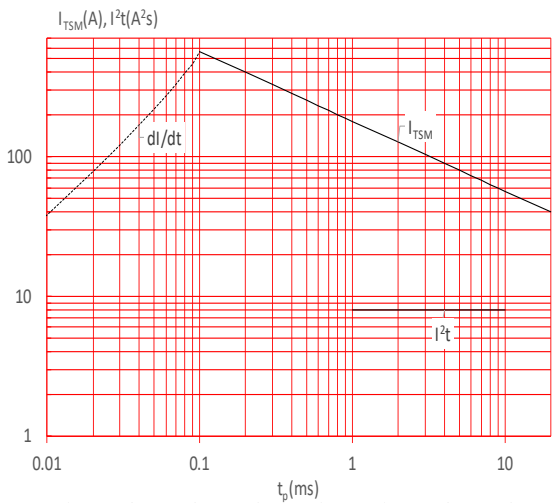
**FIG.1** Maximum power dissipation versus RMS on-state current



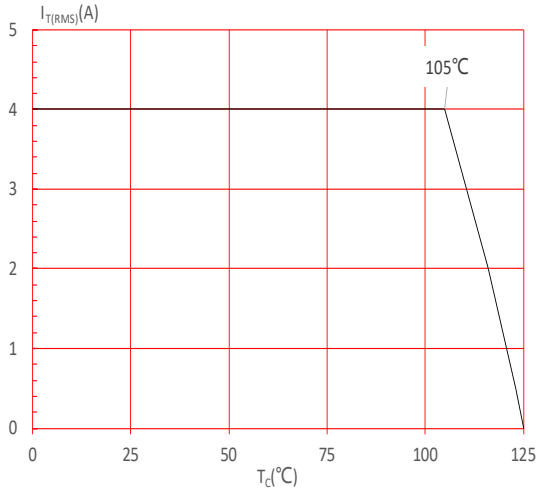
**FIG.3:** Surge peak on-state current versus number of cycles



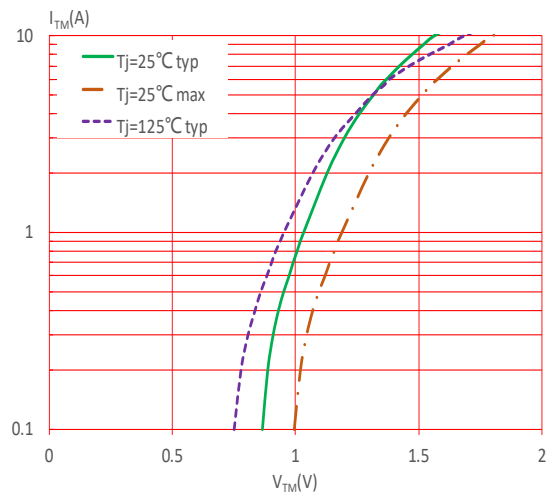
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

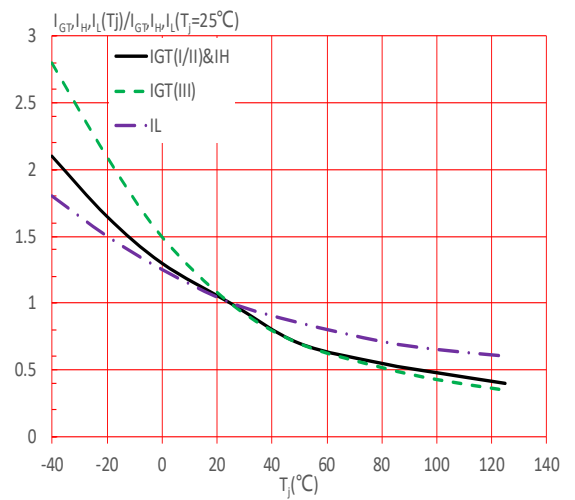
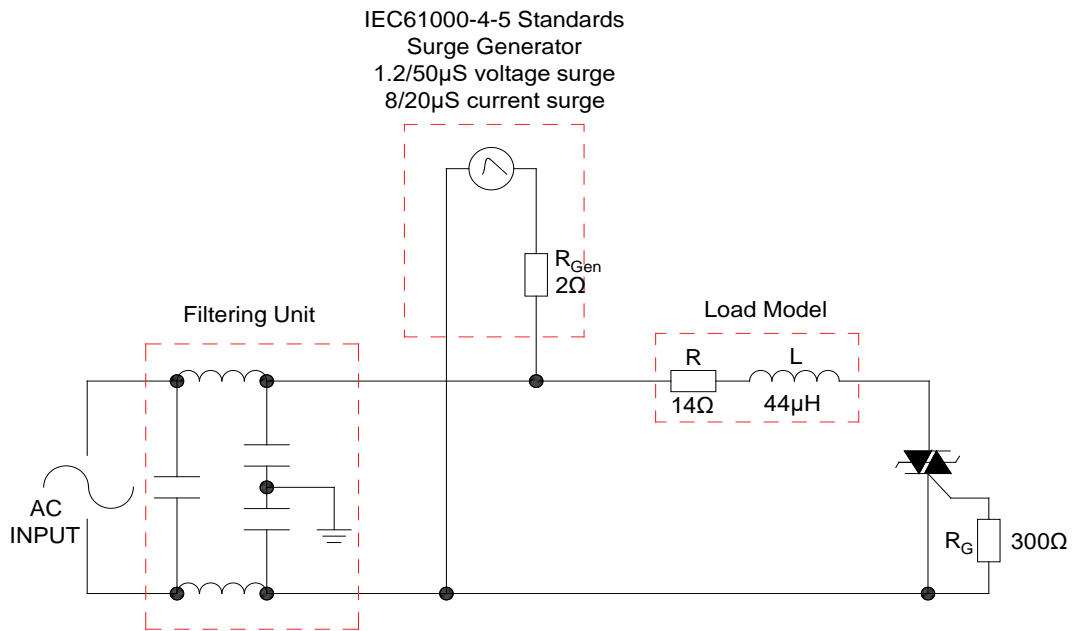


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



### SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

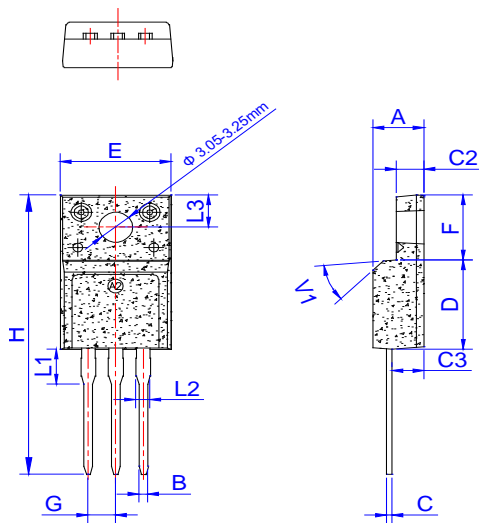
## ORDERING INFORMATION

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
ACJT425-10F	1000	25	TO-220F(Ins)	50	Tube

## Document Revision History

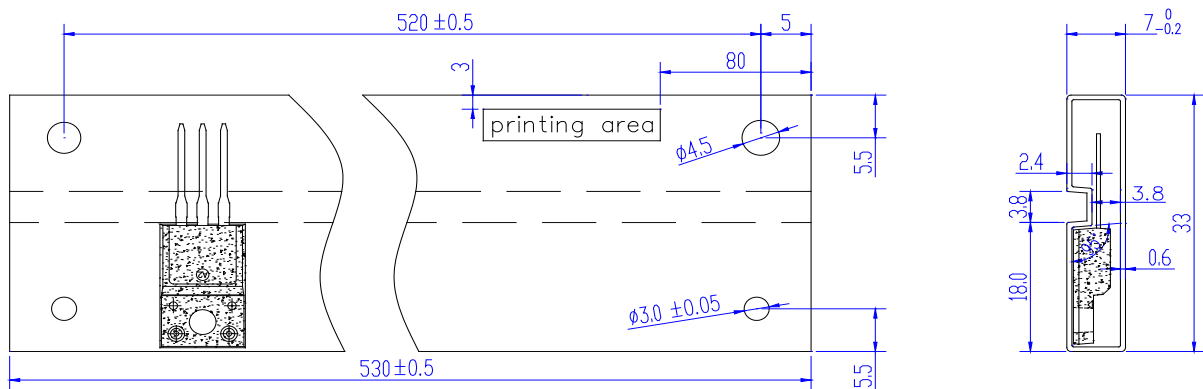
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1		45°			45°	

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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